

# Degradation mechanism of 0.15 $\mu\text{m}$ AlGaIn/GaN HEMTs: effects of hot electrons

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*Abstract – The degradation mechanisms of AlGaIn/GaN HEMTs adopting Fe and C co-doping, with high and low carbon doping concentration were investigated by means of hot-electron step stress and 24 hours' stress tests. Firstly, DC and EL characterization at room temperature are summarized, then the parametric evolution during hot-electron step stress tests at the semi-on state was compared, the assumption for the degradation mechanism is that hot-electrons activated the pre-existing traps in the buffer, attenuate the electric field in the gate drain access region and damaging the gate contact, the parametric evolution during constant stress at (-2 V, 25 V) is discussed.*

## 1. Introduction

Development of GaN High Electron Mobility Transistors (HEMTs) for telecom, radar and space applications has been improving steadily [1]–[4]. The demand for industrial-level 0.15  $\mu\text{m}$  HEMTs for low-noise and power amplifiers up to and beyond 50 GHz [5] has been enhanced by 5G and radar applications. In order to control short-channel effects, which directly determine leakage current and RF reliability [6], various approaches have been used, including back-barriers [7], C or C+Fe co-doping [8], N-polar GaN/AlGaIn channels [9] and so on. Reliability is another key issue that has to be taken into consideration during the improvement of HEMT technologies. In the working condition of RF HEMTs, the devices will experience either high electric field (off-state), or high power density (on-state) or the combination of high current density and high electric-field (semi-on state). The degradation mechanisms of the devices could be summarized as trap states generation [10], hot-electron generation [11], gate metal instabilities [12], passivation breakdown [13], inverse piezoelectric effects [14] and so on. For 0.15  $\mu\text{m}$  gate length devices, the effects of electric field have proven to be important in reliability [8]. However, there is still not enough study on the combined effects of trapping centers, high electric field and hot electrons. This work is a follow up study of [8], comparing 0.15  $\mu\text{m}$  gate length GaN HEMTs with different epi design. The effects of hot electrons on the reliability of devices are studied using electroluminescence (EL), and comparing the parametric degradation of devices during hot-electron stress. The devices were fabricated within the same batch, using the same industrial level process, with optimized gate metallization and passivation.

## 2. Experimental details

Three groups of devices were fabricated on AlGaIn/GaN heterostructures grown on SiC wafer, with gate length of 0.15  $\mu\text{m}$  and gate width of 100  $\mu\text{m}$ , processed within the same batch using a standard RF GaN HEMT process, on three kinds of epitaxial layers from different manufactures. All the samples had similar nominal peak Fe concentration i.e.  $2 \times 10^{18} \text{ cm}^{-3}$ , but different carbon doping profile, one sample is non-intentionally doped, the other two have different carbon peak concentrations:

$2 \times 10^{16} \text{ cm}^{-3}$  and  $8 \times 10^{16} \text{ cm}^{-3}$ , hereafter identified as “Fe Reference”, “Fe + Low C” and “Fe + High C”. Carbon co-doping is supposed to be helpful in reducing short-channel effects. HEMTs were submitted to on-wafer step-stress and constant voltage 24h tests. During step stress (in semi-on state, where the EL intensity is the strongest), drain voltage was increased from 0 V up to devices catastrophic breakdown in 5 V step, two minutes long each. During each stress step, drain and gate currents as well as EL intensity were monitored. After each stress step, the device was kept unbiased for 5 minutes, with a standard DC characterization and an EL image at the bias condition where there is the EL Bell peak ( $V_G = -1.5 \text{ V}$ ,  $V_D = 5 \text{ V}$ ) was taken. Afterwards, 24 hours hot-electron stress were done, with one device tested at each bias points.

## 3. Results and discussions

### 3.1 Preliminary results

DC characteristics showed that the “Fe Reference” devices have the smallest leakage current; and the “Fe + High C” device has reduced Drain Induced Barrier Lowering (DIBL) effects due to the better charge confinement due to the high carbon doping concentration, as shown in [8]. The EL intensity follows a bell shape for all devices, with the bell peak at close to -2 V, and the EL/ $I_D$  ratio in on-state ( $V_G > -1.5 \text{ V}$ ) indicating that the “Fe + Low C” samples have the highest electric field in the channel among the three kinds of devices, noticing a very small EL difference between the “Fe Reference” and the “Fe+ High C” devices.

### 3.2. hot-electron step stress

The devices were stress at  $V_G = -2 \text{ V}$ , where there is the EL peak. During stress, all the devices showed catastrophic failure at 45 V. All the devices showed less than 10 times parametric change in leakage current, and less than 10% maximum transconductance ( $g_{m,\text{max}}$ ) decrease. However, the Fe Reference wafer showed a maximum drain current ( $I_{DS,\text{max}}$ ) decrease less than 10%, while the other two devices showed 10%  $I_{DS,\text{max}}$  decrease and 10%  $R_{ON}$  increase at 35 V and 40 V, positive  $V_{TH}$  shift up to 0.5 V and 0.3 V, for “Fe-High C” and “Fe-Low C” wafer, respectively.

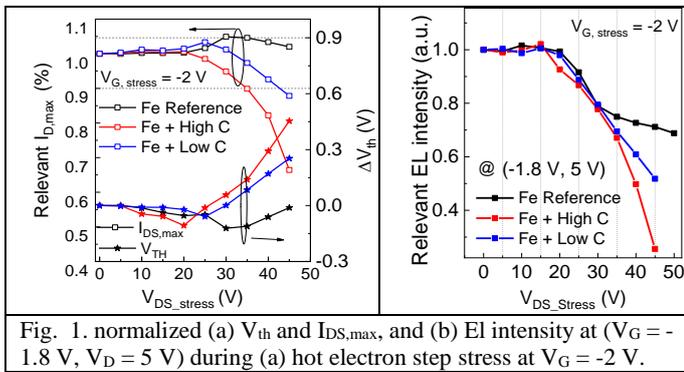


Fig. 1. normalized (a)  $V_{th}$  and  $I_{DS,max}$ , and (b) EL intensity at ( $V_G = -1.8$  V,  $V_D = 5$  V) during (a) hot electron step stress at  $V_G = -2$  V.

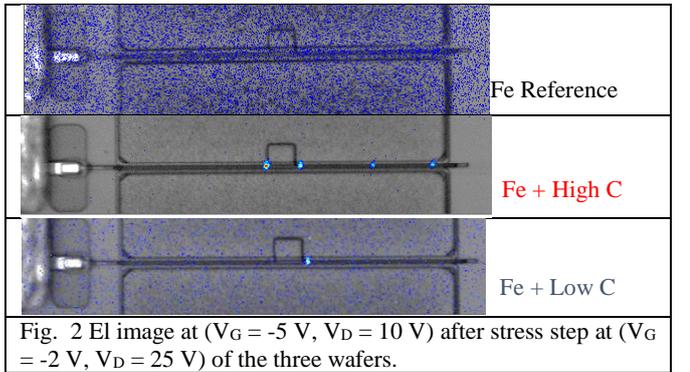


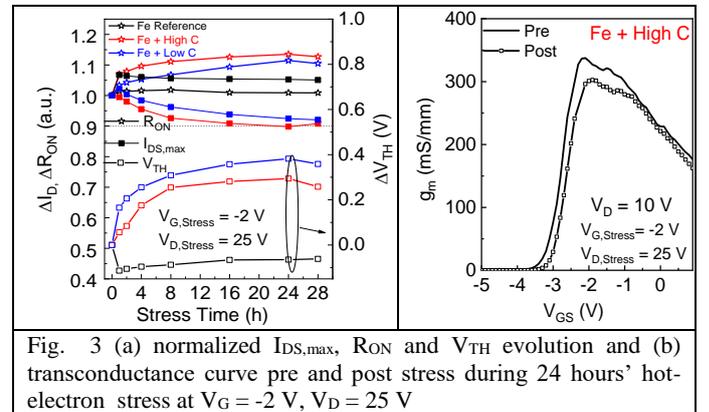
Fig. 2 EL image at ( $V_G = -5$  V,  $V_D = 10$  V) after stress step at ( $V_G = -2$  V,  $V_D = 25$  V) of the three wafers.

3.2. hot-electron 24 hours stress

24-hours stress tests were carried out, at bias points at semi-on states, with  $V_G = -2$  V and  $V_D$  from 10 V to 25 V with 5 V step. Taken the DC characteristics change during stress at (-2 V, 25 V) as an example,  $\Delta I_{DS,max}$ ,  $\Delta R_{ON}$  and  $\Delta V_{TH}$  evolution as a function of stress time are shown in Fig. 3. The Fe Reference wafer showed negligible degradation, in accordance with the results from the step stress. The assumption for the degradation mechanism is that the channel electrons got accelerated by the high electric field, which became hot electrons, some of them got energies high enough to overcome the conduction band discontinuity, entering the GaN buffer layer, which were captured by the pre-existing trapping centres owing to C related

defects, such as  $C_I$ ,  $C_N$  or  $C_{Ga}$ , leading to positive  $V_{TH}$  shift, and further  $I_{DS,max}$  decrease, and damaging the gate contact.

From Fig. 3(a), during the 1st hour stress,  $V_{TH}$  shifted by 0.1 V and 0.3 V in “Fe + Low C” and “Fe + High C” samples, respectively, this is because the “Fe + Low C” sample has less electron confinement and higher electric field compared with the “Fe + High C” wafer. However, considering the whole stress, there is more  $I_{DS,max}$  decrease and  $R_{ON}$  increase in the Fe+ High C wafer, possibly because there are more carbon related defects, as discussed in [8]. The transconductance curves before and after stress shows a small decrease in the  $g_{m,max}$  peak, proving that there is damage to the gate-drain access region close to the gate contact.



#### 4. Conclusions

The degradation mechanisms of AlGaN/GaN HEMTs adopting Fe and C co-doping is assumed to be hot-electron related. The assumption is supported by the results from hot-electron step stress tests and constant stress at (-2 V, 25 V).

#### Acknowledgements

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